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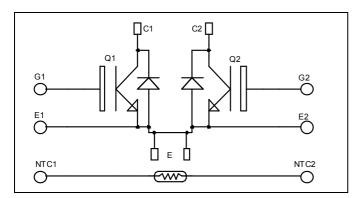






Dual common source NPT IGBT Power Module





G2 #

E2 🛍

E2 🛭

Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive T_C of V_{CEsat}
- Low profile
- RoHS Compliant

Absolute maximum ratings

| Symbol | Parameter | | Max ratings | Unit |
|-----------|---------------------------------------|----------------------|--------------|------|
| V_{CES} | Collector - Emitter Breakdown Voltage | | 1200 | V |
| ī | Continuous Collector Current | $T_c = 25^{\circ}C$ | 200 | |
| I_{C} | Continuous Conector Current | $T_c = 80^{\circ}C$ | 150 | A |
| I_{CM} | Pulsed Collector Current | $T_c = 25^{\circ}C$ | 300 | |
| V_{GE} | Gate – Emitter Voltage | | ±20 | V |
| P_{D} | Maximum Power Dissipation | $T_c = 25^{\circ}C$ | 961 | W |
| RBSOA | Reverse Bias Safe Operating Area | $T_j = 150^{\circ}C$ | 300A @ 1200V | |

C2

NTC2 8

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

| Symbol | Characteristic | Test Conditions | | Min | Typ | Max | Unit |
|---------------|--------------------------------------|---------------------------------|----------------|-----|-----|------|------|
| ī | Zara Cata Valtaga Callacter Current | $V_{GE} = 0V$ | $T_j = 25$ °C | | | 350 | ۸ |
| I_{CES} | Zero Gate Voltage Collector Current | $V_{CE} = 1200V$ | $T_j = 125$ °C | | | 600 | μA |
| V | Collector Emitter saturation Voltage | $V_{GE} = 15V$ | $T_j = 25$ °C | | 3.2 | 3.7 | V |
| $V_{CE(sat)}$ | Conector Emitter saturation voltage | $I_{\rm C} = 150 A$ | $T_j = 125$ °C | | 3.9 | | V |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C =$ | 5 mA | 4.5 | | 6.5 | V |
| I_{GES} | Gate – Emitter Leakage Current | $V_{GE} = \pm 20V, V_{CE} = 0V$ | | | | ±500 | nA |

Dynamic Characteristics

| · | Characteristic | Test Condition | is | Min | Тур | Max | Unit |
|------------------|------------------------------|--|----------------|-----|------|-----|------|
| Cies | Input Capacitance | $V_{GE} = 0V$ | | | 10.2 | | |
| C_{oes} | Output Capacitance | $V_{CE} = 25V$ | | | 1.4 | | nF |
| C_{res} | Reverse Transfer Capacitance | f = 1MHz | | | 0.75 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Swit | ching (25°C) | | 120 | | |
| T_{r} | Rise Time | $V_{GE} = 15V$ | | | 50 | | ma |
| $T_{d(off)}$ | Turn-off Delay Time | $V_{Bus} = 600V$ $I_{C} = 150A$ | | | 310 | | ns |
| T_{f} | Fall Time | $R_G = 5.6\Omega$ | | 20 | | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Swit | ching (125°C) | | 130 | | |
| T_{r} | Rise Time | $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_{C} = 150A$ | | | 60 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | | 360 | | ns |
| T_{f} | Fall Time | $R_G = 5.6\Omega$ | | | 30 | | |
| Eon | Turn-on Switching Energy | $V_{GE} = 15V$ $V_{Bus} = 600V$ | $T_j = 125$ °C | | 18 | | ma I |
| E_{off} | Turn-off Switching Energy | $I_C = 150A$ $R_G = 5.6\Omega$ | $T_j = 125$ °C | | 8 | | mJ |

Reverse diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | | Min | Typ | Max | Unit | |
|---------------------------|---|--|------------------------|------------------------|----------------|-----|------|--|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | | 1200 | | | V | |
| ī | Maximum Reverse Leakage Current | V _R =1200V | $T_j = 25$ °C | | | 500 | 4 | |
| I_{RM} | | V _R −1200 V | $T_j = 125$ °C | | | 750 | μΑ | |
| I_F | DC Forward Current | | Tc = 80°C | | 100 | | A | |
| V | Die de Fermand Weltere | I = 100 A | $T_j = 25^{\circ}C$ | | 2.1 | | V | |
| V_{F} | Diode Forward Voltage | $I_F = 100A$ | $T_{j} = 125^{\circ}C$ | | 1.9 | | v | |
| _ | D D T' | | $T_j = 25$ °C | | 95 | | | |
| t_{rr} | Reverse Recovery Time | | | $T_{j} = 125^{\circ}C$ | $T_j = 125$ °C | | 190 | |
| 0 | D. Clare | $\begin{aligned} I_F &= 100A \\ V_R &= 600V \\ di/dt &= 2500A/\mu s \end{aligned}$ | $T_j = 25$ °C | | 8.4 | | C | |
| Q_{rr} | Reverse Recovery Charge | | $T_j = 125$ °C | | 18 | | μС | |
| E _r | Reverse Recovery Energy | | $T_j = 25$ °C | | 3 | | mJ | |
| \mathbf{r}_{r} | Reverse Recovery Ellergy | | $T_{j} = 125^{\circ}C$ | | 6 | | 1113 | |



 $Temperature\ sensor\ NTC\ (\text{see application note APT0406 on www.microsemi.com for more information}).$

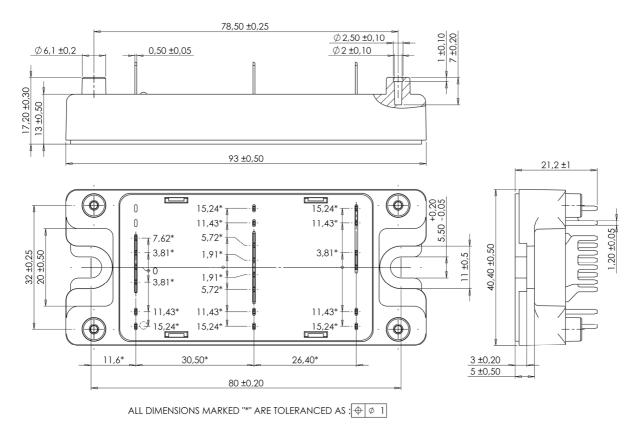
| | Symbol | Characteristic | Min | Тур | Max | Unit |
|---|----------|-----------------------------|-----|------|-----|------|
| ſ | R_{25} | Resistance @ 25°C | | 50 | | kΩ |
| Ī | B 25/85 | $T_{25} = 298.15 \text{ K}$ | | 3952 | | K |

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

| Symbol | Characteristic | | | Min | Typ | Max | Unit |
|-------------|---|-------------|-------|------|-----|------|------|
| R_{thJC} | Junction to Case Thermal Resistance | | IGBT | | | 0.13 | °C/W |
| KthJC | | | Diode | | | 0.32 | |
| V_{ISOL} | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz | | | 4000 | | | V |
| T_{J} | Operating junction temperature range | | -40 | | 150 | | |
| T_{STG} | Storage Temperature Range | | -40 | | 125 | °C | |
| $T_{\rm C}$ | Operating Case Temperature | | -40 | | 100 | | |
| Torque | Mounting torque | To heatsink | M5 | 2.5 | | 4.7 | N.m |
| Wt | Package Weight | | | | | 160 | g |

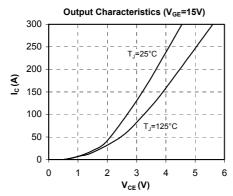
SP4 Package outline (dimensions in mm)

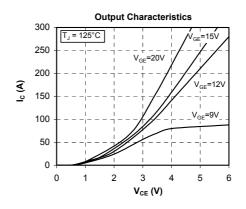


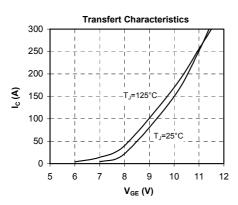
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

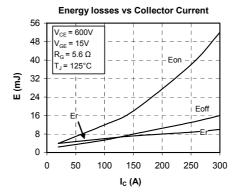


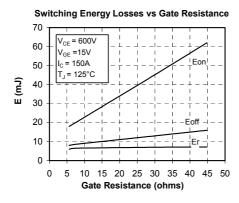
Typical Performance Curve

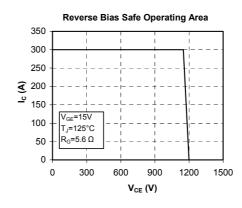


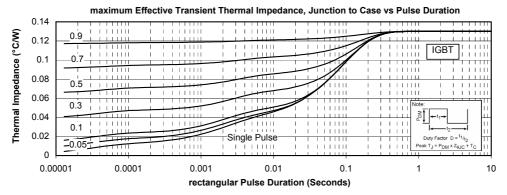




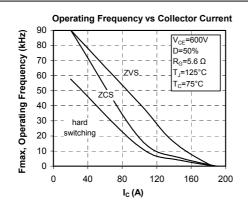


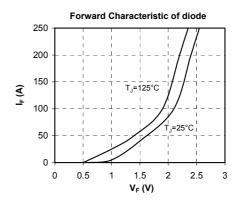


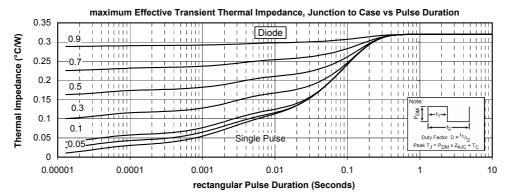














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